IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

| Priority Application Serial No |
|---|
| Priority Filing Date June 11, 1999 |
| Inventor |
| Assignee Micron Technology, Inc. |
| Priority Group Art Unit |
| Priority Examiner E. Lee |
| Attorney's Docket No |
| Title: Methods for Forming Wordlines, Transistor Gates, and Conductive Interconnects, |
| and Wordline, Transistor Gate, and Conductive Interconnect Structures |

PRELIMINARY AMENDMENT

To:

Assistant Commissioner for Patents

Washington, D.C. 20231

From:

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<u>AMENDMENTS</u>

In the Specification

At page 1, before the "Technical Field" section, insert the following paragraph in accordance with 37 C.F.R. § 1.121(b)(1)(ii):

-- RELATED PATENT DATA

This patent resulted from a divisional application of U.S. Patent Application Serial No. 09/332,271, filed June 11, 1999.--.

In the Claims

Please replace the claims with the following clean version of the entire set of pending claims, in accordance with 37 C.F.R. § 1.121(c)(1)(i). Cancel all previous versions of any pending claim.

A marked up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. § 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

CLAIMS

Please cancel claims 1-20.

- 21. A conductive line comprising:
- a polysilicon layer; and

a metal-silicide layer against the layer of polysilicon, the metal-silicide layer comprising a Group III dopant or a Group V dopant.

- 22. The conductive line of claim 21 wherein the metal-silicide layer comprises a concentration of the dopant of at least about 1 \times 10¹⁸ ions/cm³.
- 23. A metal-silicide layer comprising a Group III dopant or a Group V dopant.
- 24. The metal-silicide of claim 23 comprising a concentration of the dopant of at least about 1 \times 10¹⁸ ions/cm³.

- 25. A programmable-read-only-memory device comprising:
- a first dielectric layer over a substrate;
- a floating gate over the first dielectric layer;
- a second dielectric layer over the floating gate;
- a conductive line over the second dielectric layer; and
- a metal-silicide layer over the conductive line, the metal-silicide layer comprising a Group III dopant or a Group V dopant.
- 26. The programmable-read-only-memory device of claim 25 wherein the device is an EPROM.
- 27. The programmable-read-only-memory device of claim 25 wherein the device is an EEPROM.
- 28. The programmable-read-only-memory device of claim 25 wherein the metal-silicide layer comprises a concentration of the dopant of at least about 1×10^{18} ions/cm³.

REMARKS

Claims 1-20 are canceled. Claims 21-28 are pending in the application, and Applicant requests examination of such pending claims.

The signature of Klaus Florian Schuegraf is missing from the filed declaration as an "uncooperative inventor". Accordingly, this application is filed with an attached granted Petition pursuant to 37 C.F.R. §1.47(a) due to an "uncooperative inventor" and a declaration signed by the cooperative inventor. The enclosed granted Petition under §1.47(a) is from the parent file (U.S. Patent Application Serial No. 09/332,271).

Respectfully submitted,

Dated: 0-4-01

Bv:

D. Brent Kenady Reg. No. 40,045

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| Inventor Klaus Florian Schuegraf et al. |
| Assignee Micron Technology, Inc. |
| Priority Group Art Unit |
| Priority Examiner E. Lee |
| Attorney's Docket No MI22-1741 |
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| Interconnects, and Wordline, Transistor Gate, and Conductive Interconnect |
| Structures |

VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING PRELIMINARY AMENDMENT

In the Specification

The replacement specification paragraphs incorporate the following amendments. <u>Underlines</u> indicate insertions and strikeouts indicate deletions.

At page 1, before the "Technical Field" section, insert the following paragraph in accordance with 37 C.F.R. § 1.121(b)(1)(ii):

--RELATED PATENT DATA

This patent resulted from a divisional application of U.S. Patent Application Serial No. 09/332,271, filed June 11, 1999.--.

In the Claims

The claims have been amended as follows. <u>Underlines</u> indicate insertions and strikeouts indicate deletions.

Please cancel claims 1-20.